

IN THE CLAIMS

1. (Canceled)
2. (Canceled)
3. (Canceled)
4. (Canceled)
5. (Canceled)
6. (Canceled)
7. (Canceled)
8. (Canceled)
9. (Canceled)
10. (Canceled)

11. (Currently Amended) A method of manufacturing an electronic device, comprising the steps of:

~~(a) preparing a ReO_3 layer having a (001) orientation;~~

(a-1) forming a MgO layer having a (001) orientation, on an amorphous layer,

(a-2) forming a ReO_3 layer having a (001) orientation, on said MgO layer; and

(b) forming an oxide ferroelectric layer having a perovskite structure and a (001) orientation, on said ReO_3 layer.

12. (Canceled)

13. (Canceled)

14. (Canceled)

15. (Currently amended) The method of manufacturing an electronic device according to claim 44 11, wherein at least one of said steps ~~(a-1-2)~~ (a-1), (a-2) and (b) is done by metalorganic chemical vapor deposition (MOCVD).

16. (Currently amended) The method of manufacturing an electronic device according to claim 15, wherein all of said steps ~~(a-1-2)~~ (a-1), (a-2) and (b) are done by MOCVD.

17. (Original) The method of manufacturing an electronic device according to claim 15, wherein said MOCVD is executed at a substrate temperature of 620°C or lower.

18. (Original) The method of manufacturing an electronic device according to claim 15, wherein said MOCVD uses, as organometal raw material, a dipivaloilmethanate (DPM) compound of metal or an iso-proxy (i-PrO) compound of metal.

19. (Currently amended) The method of manufacturing an electronic device according to claim 44 11, wherein at least one of said steps ~~(a-1-2)~~ (a-1), (a-2) and (b) is done by sputtering.

20. (Original) The method of manufacturing an electronic device according to claim 11, further comprising the step of: (c) forming at least one upper electrode layer on said oxide ferroelectric layer.